

Contamination policy and General rules

Savitha

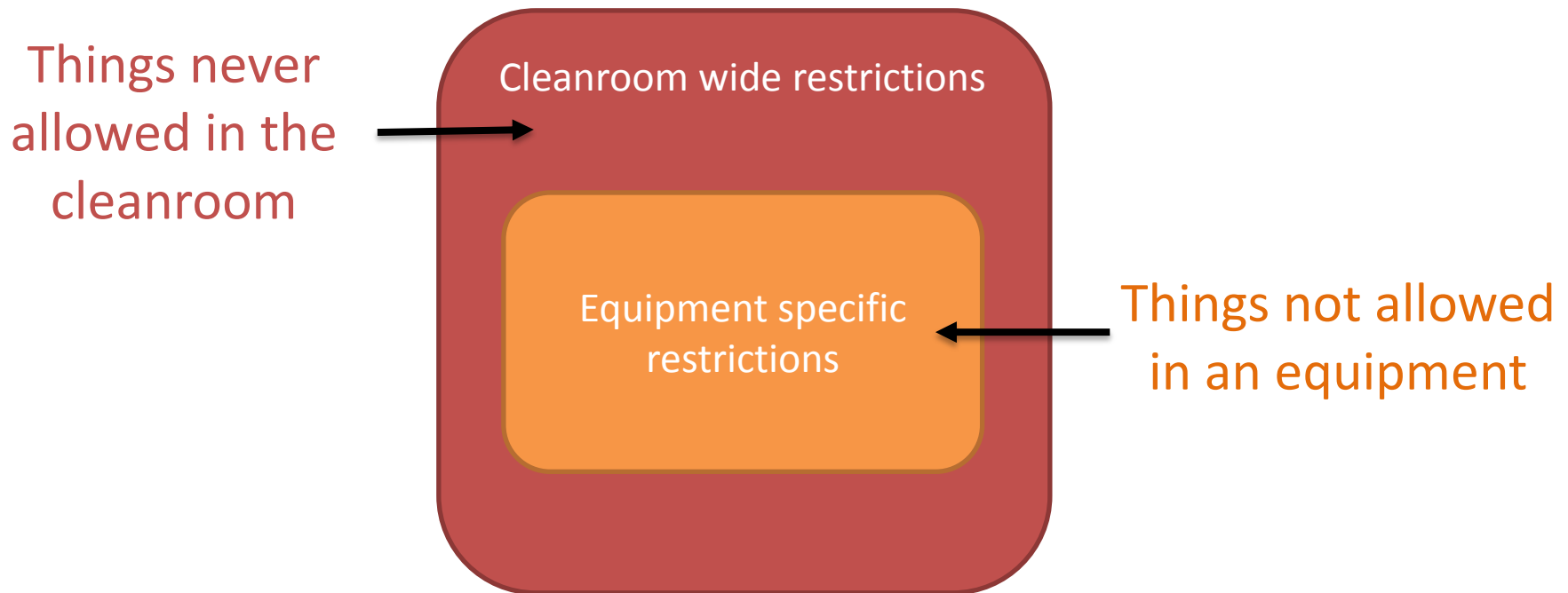
30th Jan 2019

Problem of Cross Contamination

- Definition:
 - Transfer of undesirable materials from one equipment to another.
- Occurs because of:
 - Incompatible process flows
 - Move from cleanest step to dirty step (downstream). Never upstream.
 - Irresponsible user behavior
 - As long as my work gets done, it is not my problem.
- Causes:
 - Poor device performance and reliability
 - Poor repeatability of processes
 - Expensive repair/downtime of equipment

What is the Contamination Policy?

- Outlines NNFC's policy on allowed/disallowed materials in the cleanroom & each of the equipment



Cleanroom-wide Restrictions

- Sulfur
 - Clogs the pumps and valves.
- PDMS
 - Please use PV-lab and polymer lab for processing these.
- Fast diffusing (Cu, Zn, Fe, Mn, etc.), toxic metals (Cd, Sb, Se, As, Hg, etc.), their alloys
 - Entry allowed only on a case-by-case basis
- Only approved photoresists allowed in Litho bay
 - Standard list available at FOM (purchase supplies)
- Only approved chemicals allowed at the wet bench
 - List available at FOM (purchase supplies)

GaAs, InP and PZT

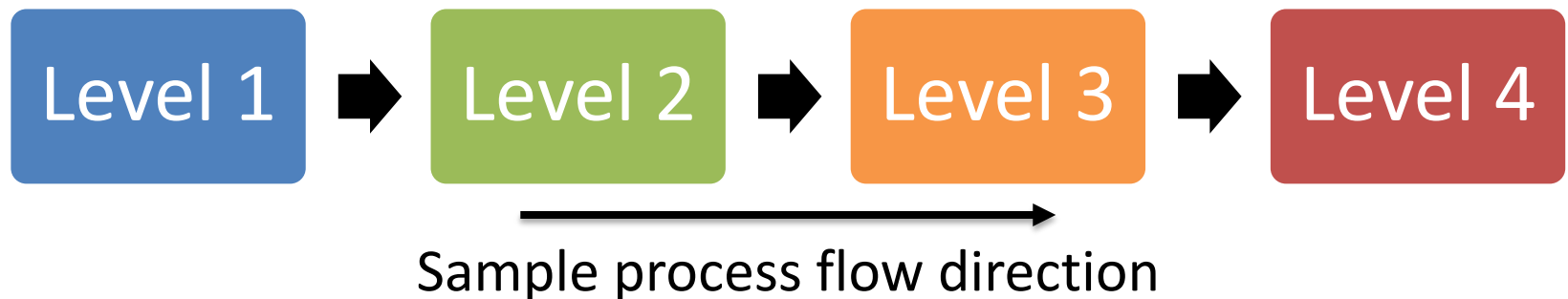
- Please use PV and Polymer lab for these materials
- If these materials need to be processed inside the cleanroom, please contact the material entry committee at savithap@iisc.ac.in

New Materials Entry

- Need special permission for non-standard chemicals/photoresists/wafers/targets etc.
 - No exceptions...
- Procedure to seek permission for bringing in new material is available at NNFC website.
 - Email Savitha (savithap@iisc.ac.in) with
 - Prior process
 - Post process
 - Hazardous nature analysis: Provide in detail the dangers to be expected from the material and also the required PPE
 - Why the cleanroom need to be used

Equipment-Specific Restrictions

- Each equipment has a contamination level
- Based on the contamination level, entry of materials and samples are restricted.
- Basic idea
 - Sample move from low-contamination to high-contamination



Classification of Equipment (Levels)

LEVEL 1 (Color code: Light blue)	• New diced samples/wafer-pieces • Samples from Level 1 equipment • Samples after RCA clean on Level 2 wet-bench • No samples with metals	 RCA clean in level 1 wet bench
LEVEL 2 (Color code: Green)	• Samples processed in level 2 • Samples from lithography • No samples with metals	
LEVEL 3a (Color code: White in orange)	• Samples processed in Level 3 deposition equipment only • Samples with metal allowed but no exposed metal and no fast-diffusing metals.	 Not allowed
LEVEL 3 (Colour code: Orange)	• Samples with any metal • Fast-diffusion metals cannot be exposed and can only be processed at room temperature	
LEVEL4 (Color code: Red)	• Samples processed outside NNfC (PV Lab, etc.) • Sample with unknown lineage.	

Please note that samples processed in Level 3 will not be accepted in level 2 or 1

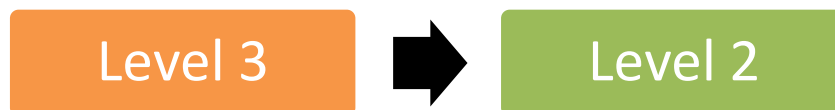
Process Flow Rules

- Sample always move downstream
 - from a lower level to a higher level
- Exceptions: Lithography and inline characterization
 - But make sure the chuck is clean before you put samples on it
- “Dirty” substrates always assumed to be “metal-contaminated”
 - E.g. glass slides always start at level 3 or above
- Special process flows exist for “jumping” from a higher level to a lower level
 - However, “jumps” have to be evaluated on a case-by-case basis

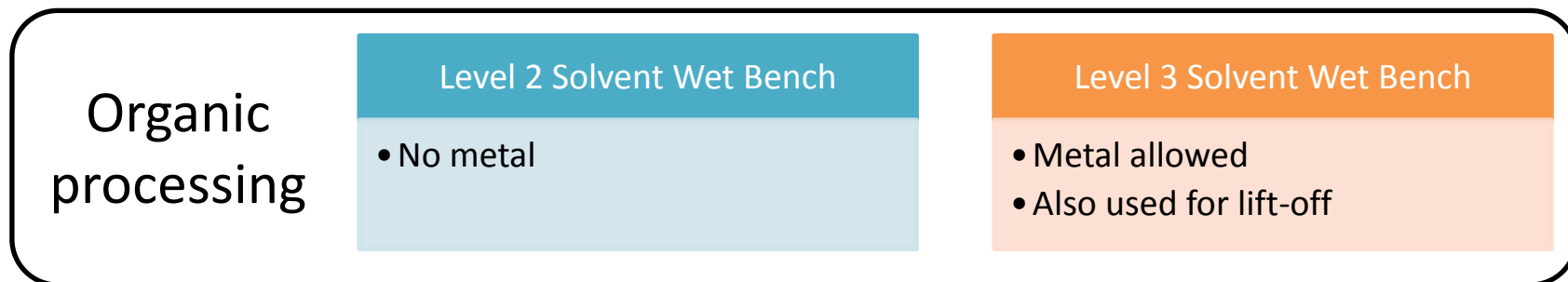
Process Flow Rules ...

- Direct entry to FirstNano atmospheric furnaces only from Level 1 wet benches
 - Except for 1 tubes which are level 2
- Some machines have multiple levels, depending on recent history
 - E.g. PECVD.

PECVD chamber clean



- Separate wet benches for “metal-free” & “metal-contaminated” organic processing
 - Organic == involving acetone/IPA/methanol/ethanol



Chemical Wet Benches (CWB)

Old Name	New Name	Level
Preclean bench	CWB Acid Clean (BULK process only)	1
Chemical wet bench general	CWB Acid clean	1
Chemical wetbench CMOS non-metal	CWB Acid semi-clean	2
Electroplating bench/General wet bench 2	CWB Solvents/bases semi-clean	2
Chemical wetbench MEMS non-metal (BULK processes)	CWB Acid semi-clean bulk (Metal etching allowed)	3
Chemical Wetbench CMOS metal	CWB Acid Metal	3
Solvent bench	CWB Solvent/bases	3
	CWB HF vaporiser	3

No wet bench available at Level 4

Samples from Level 4 equipment to be processed at PV or polymer processing lab

Wet Etches with **NO METAL**

CWB Acid clean (Level 1)

- **Usage:** Oxide, oxynitride, PSG and BSG etching + RCA and Piranha
- **Allowed Samples:** New wafers or wafers processed in Level 1 First nano furnace/RTP-2

CWB Solvents/bases semi-clean (Level 2)

- **Usage:** Solvent processing of samples from Lithography having NO metal contamination + clean TMAH
- **Allowed samples:** To/from Level 2 equipment + Oxide/nitride from PECVD (after chamber clean)

CWB Acid semi-clean (Level 2)

- **Usage:** RCA clean to jump from Level 3a to Level 2
- **Allowed samples:** To/from Level 2 equipment + To/from Level 3 equipment after metal etch.

Wet Etches **with Metal**

CWB Acid semi-clean bulk + Acid Metal (Level 3)

- **Usage:** Wet etching of metals, Electroplating of Gold, Metal Lift off, Mask clean
- **Allowed Samples:** From Level 3 tools like sputtering, e-beam evaporation, RIE-Cl

CWB Solvent/bases (Level 3)

- **Usage:** KOH etching, TMAH etch for gold contaminated samples
- **Allowed sample:** from Level 3 tools like sputtering, e-beam evaporation, RIE-Cl

HF Vaporizer (Level 3)

- **Usage:** Vapor etch using HF

CPD (Level 4)

- **Usage:** Releasing MEMS structures

Use of tweezers, gloves and glassware

- Cleanroom provides tweezers only for Level 1/2 RCA
 - User to have their own tweezer for other levels
- Only quartz glassware are allowed on Level 1 and Level 2 acid processes
 - No glass, no borosilicate glass, & no pyrex.
- Metal tweezers NOT allowed in Level 1 and Level 2 wet benches
- Use only dedicated tweezer/gloves for each level
 - DO NOT mix.
 - If you have made a mistake please inform.
- Gold processing always has to be done on separate glassware

Levels of First Nano/RTP/Tempress furnaces/CPD

Level 1

- Si oxidation and dopant diffusion
- Drive-in/sintering
- RTP-2 for oxide and oxynitride

Level 2

- LPCVD SiN_x
- Poly and Epi Si/Ge
- Low-temperature oxides (TEOS)
- BSG & PSG
- Metal Annealing (Semi clean: Al, Ti, W only)

Level 3

- Poly Epi-Si/Ge deposition (Nanowire growth on metal containing samples), Tempress furnaces

Level 4

- RTP-1 for metal contact anneal, CPD

Lithography and Inline Characterization

- Lithography and Inline Characterization are level-less
- Samples from any level can be processed
 - Please make sure chucks are clean

Dry Etch bay

- DRIE: Level 3a: Samples with metal allowed, but should not be exposed to the process
- RIE-F: Level 3a: Samples with metal allowed, but should not be exposed to the process
- RIE-Cl: Level 3
- PECVD: Level 2/3: For level 2 process, please do a chamber clean before
- ALD: Level 3

Thin films bay

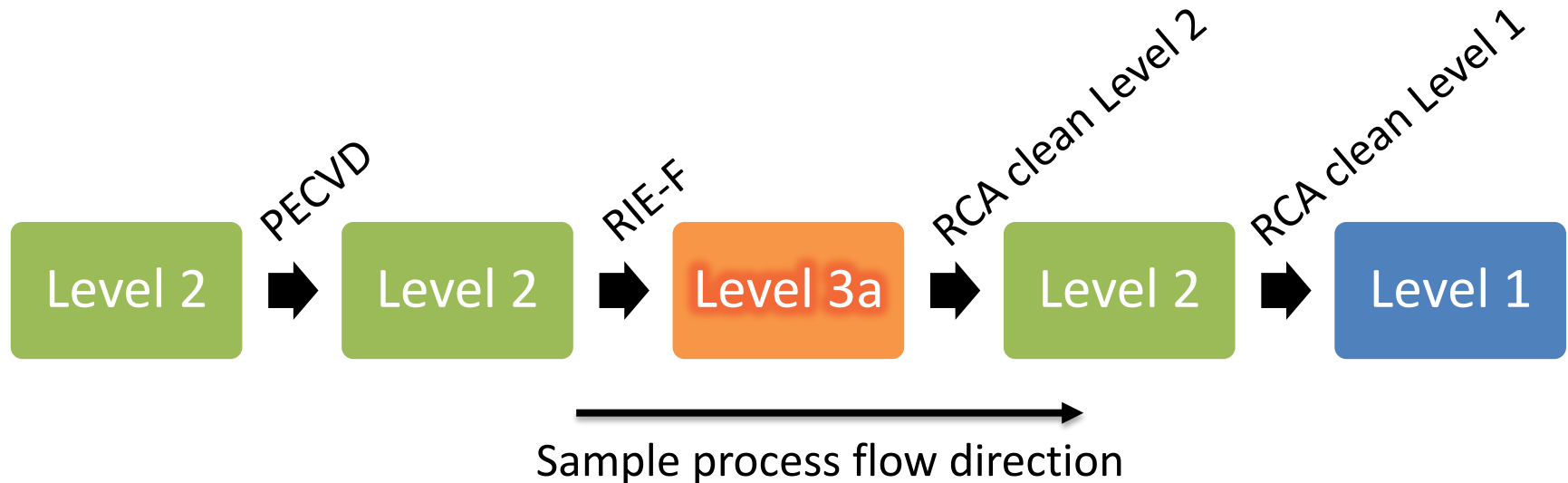
- Tecport Dielectric Sputtering: Level 2
- Tecport Metal Sputtering, Tecport E-beam evaporator, Leybold E-beam evaporator: All are Level 3

Allowed or Not-Allowed: Example 1

- Level 2 sample
 - Nitride deposition in PECVD
 - Nitride etch in goes RIE-F
 - Anneal in First Nano furnace

Equipment	Level
PECVD	Level 2/3
RIE-F	Level 3a
Diffusion Furnace	Level 1

Do chamber-clean for Level 2 PECVD

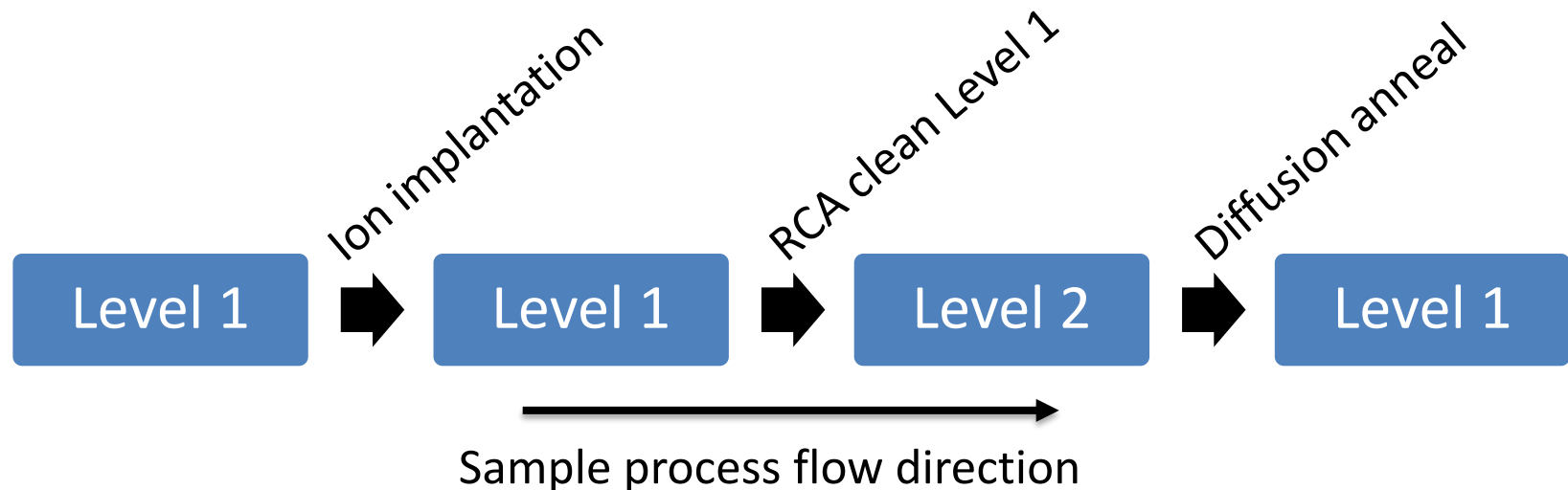


Allowed or Not-Allowed: Example 2

- Level 1 Si sample
 - Goes out for ion implantation
 - To be annealed in FirstNano diffusion furnace

Equipment	Level
Ion-implantation	Level ?
Diffusion Furnace	Level 1

Ion implantation at reputed place is expected to be clean



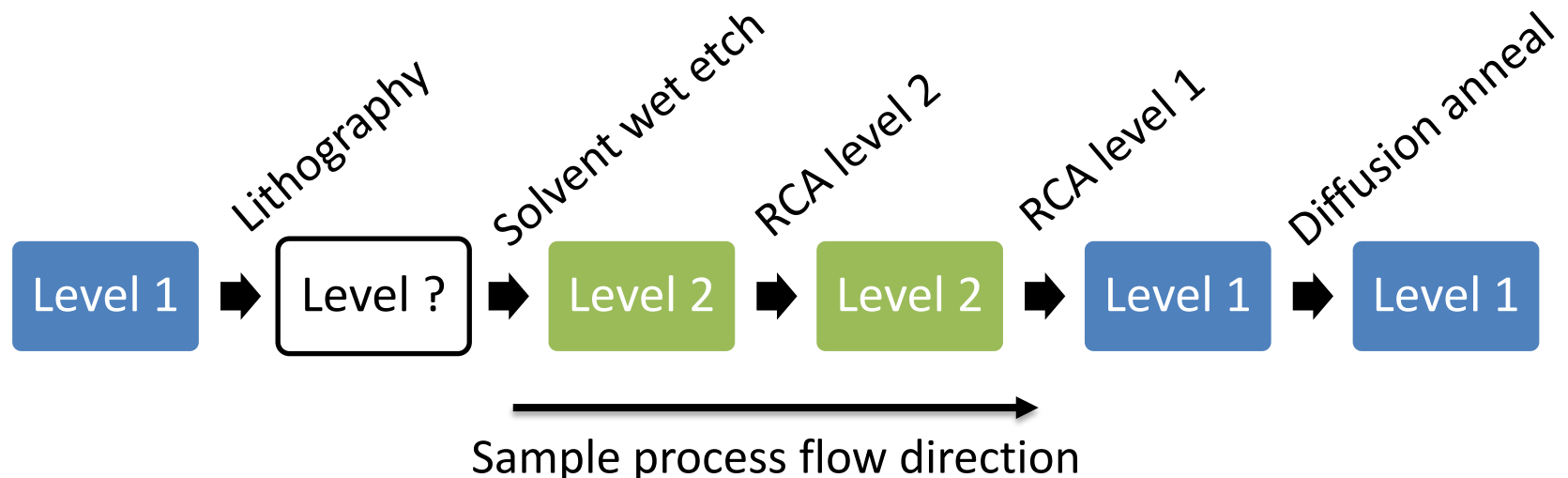
Allowed or Not-Allowed: Example 3

- Level 1 SiO₂ coated Si sample
 - Goes to lithography
 - Solvent wet-bench
 - Anneal in FirstNano diffusion furnace

Equipment	Level
Lithography	Level ?
Solvent etch	Level 2
Diffusion furnace	Level 1

Lithography is level-less process.

Solvent clean is level 2. Need RCA clean to “jump up” Level 1

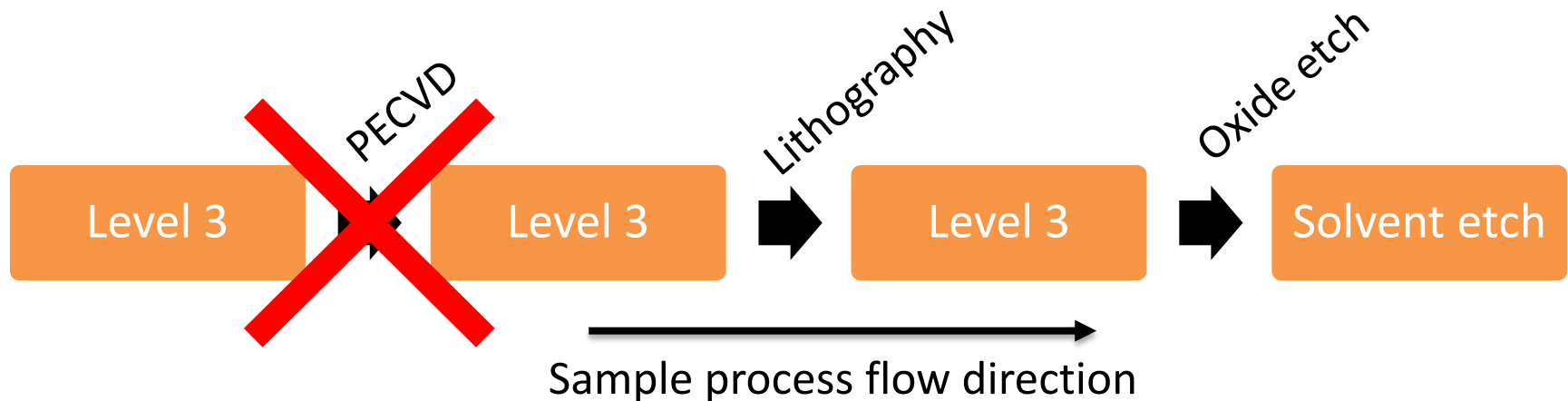


Allowed or Not-Allowed: Example 4

- Cu_2O containing sample
 - Deposit PECVD oxide on top
 - Lithography
 - Solvent etch

Equipment	Level
PECVD	Level 2/3
Lithography	Level ?
Wet Etch	Level 3

Level 3 PECVD will be exposed to Cu



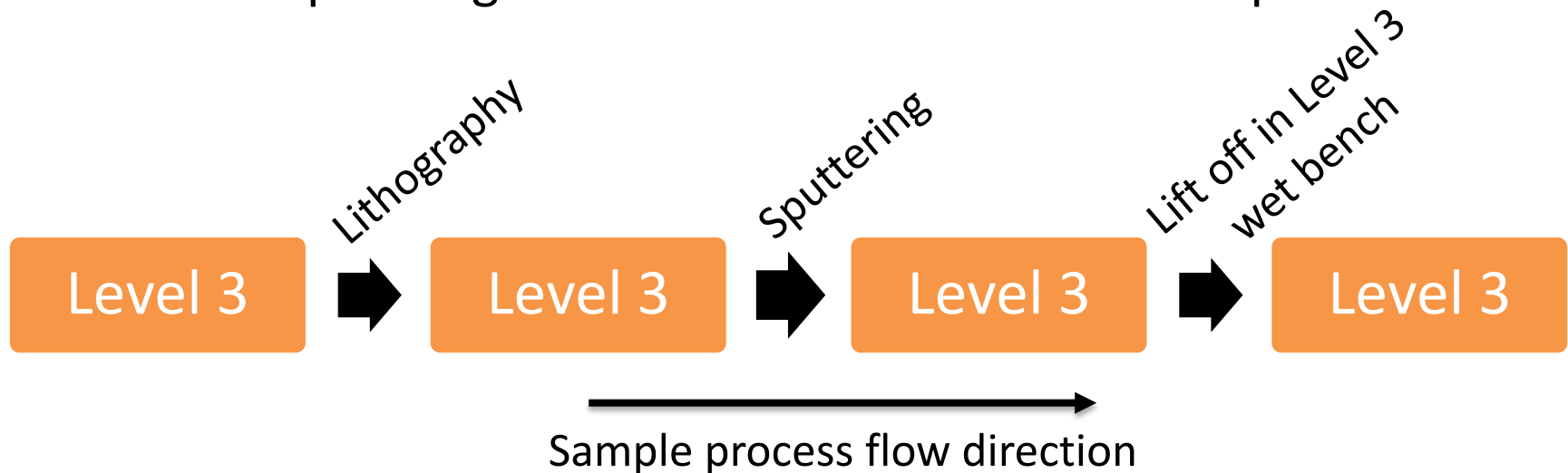
Allowed or Not-Allowed: Example 5

- Cu_2O containing sample

- Lithography
- Sputter oxide on top
- Lift-off

Equipment	Level
Lithography	Level ?
Sputter Tool	Level 3
Lift-off	Level 3

Cu_2O is allowed in level 3 sputter tool. However need separate glassware for lift-off with Cu-sample



Not sure about your process flow?

- For evaluation , please send an email to savithap@iisc.ac.in with your detailed process flow
 - Need at least a 7 day advance notice to respond.
 - No last minute permissions